

Electronic Acknowledgement Receipt

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Application Number:	10565621
International Application Number:	
Confirmation Number:	2319
Title of Invention:	Stacked structure and production method thereof
First Named Inventor/Applicant Name:	Hubert Moriceau
Customer Number:	90678
Filer:	Jasper W. Dockrey
Filer Authorized By:	
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Application Type:	U.S. National Stage under 35 USC 371

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File Listing:

Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)
1	NPL Documents	Demeester_et_al_Epitaxial_Lift-Off_and_Its_Aplns.pdf	1057147 e514a67ef257a1b59cd7bd60d39af05986a40b7c	no	13

Warnings:

Information:

2	NPL Documents	Denteneer_et_al_Hydrogen_Diffusion_and_Passivation_of_Silicon_Thin_Films.pdf	299205	no	5
			9a4be7616268e450c107930a24c1956759a6b8ba		
Warnings:					
Information:					
3	NPL Documents	Denteneer_et_al_Structure_and_Properties_of_Hydrogen-Impurity_Pairs.pdf	342276	no	4
			a91ff56edf7086aa9e74cdcafb2827aa5ee12a8a		
Warnings:					
Information:					
4	NPL Documents	DiCioccio_et_al_Silicon_Carbide_on_Insulator_Formation.pdf	130526	no	2
			f3f564678f1bb826e45d975574c99b2989092ac4		
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5	NPL Documents	Dirks_AG_et_al_Columnar_Microstructure_in_Vapor_Deposited_Thin_Films.pdf	1187199	no	15
			6b089b5565b3cbe5389aaa781ca71cc23e78fc0		
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6	NPL Documents	Duo_et_al_Comparison_Between_The_Different.pdf	821079	no	6
			6519e4d26a98aed37e9d54f06b517ddaab7ea02d		
Warnings:					
Information:					
7	NPL Documents	Duo-et-al-Evolution-of-Hydrogen-and-Helium_1.PDF	549396	no	6
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8	NPL Documents	Eaglesham_White_et_al_Equilibrium_Shape_of_Si.pdf	272298	no	4
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9	NPL Documents	EerNisse_E-Compaction_of_Ion-Implanted_Fused_Silica.pdf	768866	no	8
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10	NPL Documents	EerNisse_EP-Role_of_Integrated_Lateral_Stress_In_Surface_Deformation_of_He_Implanted_Surfaces.pdf	801341	no	9
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11	NPL Documents	Evans_JH_An_Interbubble_Fracture_Mechanism_Of_Blister.pdf	869679	no	12
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			6e4546b0647157aca4b2ed11123fd63bbeb1fd43		
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13	NPL Documents	Feng_et_al_Generalized_Formula_For_Curvature.pdf	137308	no	3
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14	NPL Documents	Garner_DM-The_Fabrication_Of_A_Partial_SOI_Substrate.pdf	376649	no	6
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15	NPL Documents	Gerasimenko_N-Infrared_Absorption_of_Silicon_Irradiated_by_Phrotons.pdf	423407	no	7
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16	NPL Documents	Ghandi_Sorab-VSLI_Fabrication_Principles-Silicon_and_Gallium_Arsenide.pdf	145184	no	4
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17	NPL Documents	Greenwald_AC-Pulsed-Electron-Beam_Annealing_of_Ion-Implantation_Damage.pdf	364299	no	4
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19	NPL Documents	Guilhalmenc_C_et_al_Characterization_By_Atomic_Force_Microscopy_of_the_SOI_Layer.pdf	266316	no	4
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20	NPL Documents	Haisma_et_al_Silicon_on_Insulator-Wafer_Bonding.pdf	1279237	no	18
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21	NPL Documents	Hamaguchi_et_al_Device_Layer_Transfer_Technique.pdf	157984	no	3
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23	NPL Documents	Henttinen_et_al-Mechanically_Induced_Si_Layer.pdf	248942	no	3
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25	NPL Documents	IBM_Technical_Disclosure_Bulletin-Isolation_By_Inert_Ion_Implantation.pdf	31620	no	1
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27	NPL Documents	Jap-OA-Dated-10-25-07-2002-581572.pdf	209378	no	5
			a150ec5658266e19d62f54064cf2c605eea9a495		
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28	NPL Documents	Jaussaud_C_et_al-Microstructure_of_Silicon_Implanted_With_High_Dose_Oxygen_Ions.pdf	393224	no	3
			fbcd5ae0b610d798f76fcd6338055485e0fe4e11		
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29	NPL Documents	Johnson-High_Fluence_Deuteron_Bombardment_of_Silicon.pdf	837642	no	9
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30	NPL Documents	Jones_KS_et_al-A_Systematic_Analysis_of_Defects_in_Ion_Implanted_Silicon.pdf	2789593	no	35
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31	NPL Documents	Jones_et_al_Enhanced_elimination_of_implantation_damage_upon_exceeding_the_solid_solubility.pdf	379786	no	4
			d346990b4884595096dba89caa0d8f3875ded705		
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32	NPL Documents	Kamada_et_al-Observation_of_Blistering_and_Amorphization_on_Germanium_Surface_After_keV.pdf	519461	no	6
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34	NPL Documents	Komarov_et_al-Crystallographic_Nature_and_Formation_Mechanisms_of_Highly_Irregular_Structure.pdf	687131	no	9
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35	NPL Documents	Kucheyev_et_al-Ion_Implantation_Into_GaN.pdf	3044381	no	58
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39	NPL Documents	Liu_et_al-Ion_Implantation_in_GaN_at_Liquid-Nitrogen_Temperature.pdf	461874	no	6
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42	NPL Documents	Maleville_C_Wafer_Bonding_and_High-Implantation.pdf	266110	no	6
			47c85fa696b27cfad7abd3c57423cfa0bba003ba3		
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43	NPL Documents	Manuaba_A-Comparative_Study_on_Fe_Ni_Cr_P_Metallic_Glass_and_Its_Polycrystalline_Modification.pdf	1160732	no	11
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46	NPL Documents	Mishima_Y_and_T_Yagishita_Investigation_Of_The_Bubble_Formation.pdf	165000	no	3
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47	NPL Documents	Miyagawa_S_et_al-Helium_Reemission_During_Implantation_of_Silicon_Carbide.pdf	375866	no	5
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48	NPL Documents	Miyagaw_S_et_al-Surface_Structures_of_Silicon_Carbide_Irradiated_With_Helium_Ions.pdf	774178	no	9
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			add11312cfd8fb9227d8c8e17710ed952c95e94		
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51	NPL Documents	Moriceau_H_et_al_A_New_Characterization_Process_Used_To.pdf	303042	no	6
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55	NPL Documents	Munteanu-et-al-Detailed-Characteristics-of-Unibond-Material.pdf	186594	no	4
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56	NPL Documents	Myers_DR-The_Effects_of_Ion-Implantation_Damage_on_The_First_Order_Raman_Spectra.pdf	676976 58022efa3c3a0c9831528800a03bd1b7e34d2f7c	no	7
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58	NPL Documents	Nichols_C_et_al_Properties_of_Hydrogen_in_Crystalline_Silicon.pdf	740397 16eb72d90c4ec2b7d57db6c180d2ea0d18c5bd78	no	4
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59	NPL Documents	Nicoletti_S_et_al_Bi-Epitaxial_YBCO_Grain_Boundary_Josephson_Junctions.pdf	869860 06a47a30171ce37d689712bbd7925f8e873df226	no	13
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Total Files Size (in bytes):			32502614		
<p>This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503.</p> <p><u>New Applications Under 35 U.S.C. 111</u> If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.</p> <p><u>National Stage of an International Application under 35 U.S.C. 371</u> If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.</p> <p><u>New International Application Filed with the USPTO as a Receiving Office</u> If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.</p>					